

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	10/811553	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 07:14
L2	0	"10811553"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 07:14
L3	133	('mram' access adj memory) with (stop\$3 near3 (layer film))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 07:48
L4	18	3 and bottom adj electrode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 07:48
L5	614	('mram' access adj memory) with ((stop\$3 etch\$3) near3 (layer film))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 07:48

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	16	('mram' access adj memory) with ((stop\$3 etch\$3) near3 (layer film)) with (bottom electrode).clm.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/07/11 08:17

L6	68	3 and electrode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/07/11 07:48
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